





### N-CHANNEL ENHANCEMENT MODE FIELD MOSFET

# **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = 25°C
60V	$3.0\Omega @ V_{GS} = 10V$	400mA
	4.0Ω @ V <sub>GS</sub> = 5V	330mA

## **Description and Applications**

These N-Channel enhancement mode field effect transistors are produced using DIODES proprietary, high density, uses advanced trench technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. These products are particularly suited for low voltage, low current applications such as small

Load switching

## **Features and Benefits**

- N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate, 1.2kV HBM
- Lead, Halogen and Antimony Free, RoHS Compliant
- "Green" Device (Notes 1 and 2)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

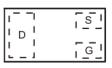
- Case: DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.001 grams (approximate)

#### DFN1006-3









Top View

Equivalent Circuit

Top View

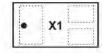
### **Ordering Information** (Note 3)

Part Number	Case	Packaging
2N7002XFB-7	DFN1006-3	3000/Tape & Reel

Notes:

- 1. No purposefully added lead. Halogen and Antimony Free.
- 2. Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb203 Fire Retardants.
- 3. For packaging details, go to our website at http://www.diodes.com

# **Marking Information**



X1 = Product Type Marking Code

Top View Dot Denotes Drain Side

Date Code Key

Year	200	9	2010		2011	20	12	2013		2014	- 2	2015
Code	W		Χ		Υ		Z	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings**

Characteris	tic	Symbol	Value	Units	
Drain-Source Voltage		V <sub>DSS</sub>	60	V	
Gate-Source Voltage		$V_{GSS}$	±20	V	
Continuous Drain Current (Note 4) V <sub>GS</sub> = 10V	Steady State	$T_A = 25$ °C $T_A = 70$ °C	ID	260 210	mA
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	Steady State	$T_A = 25$ °C $T_A = 70$ °C	I <sub>D</sub>	400 310	mA

### **Thermal Characteristics**

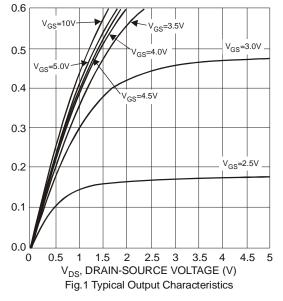
Characteristic	Symbol	Value	Units
Power Dissipation, @T <sub>A</sub> = 25°C (Note 4)	$P_{D}$	430	mW
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C (Note 4)	$R_{ heta JA}$	290	°C/W
Power Dissipation, @T <sub>A</sub> = 25°C (Note 5)	$P_{D}$	840	mW
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C (Note 5)	$R_{ heta}$ JSA	147	°C/W
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	°C

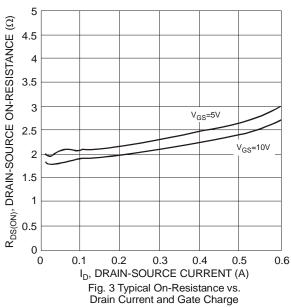
# Electrical Characteristics @TA = 25°C unless otherwise specified

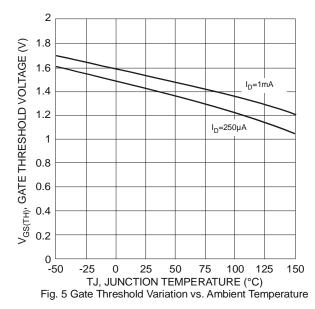
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>	-	=	0.1	μA	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Body Leakage	I <sub>GSS</sub>	-	-	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)			_	_			
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.2	-	2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance			2.1	3.0	Ω	$V_{GS} = 10V, I_D = 0.115A$	
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	-	2.3	4.0		$V_{GS} = 5V, I_D = 0.1115A$	
Forward Transfer Admittance	Y <sub>fs</sub>	80	320	-	mS	$V_{DS} = 10V, I_D = 0.115A$	
Diode Forward Voltage	V <sub>SD</sub>	-	0.7	1.0	V	$V_{GS} = 0V, I_S = 0.115A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C <sub>iss</sub>	1	25	-	pF		
Output Capacitance	Coss	-	4,7	-	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	2.5	-	pF	1	
Turn-On Delay Time	t <sub>D(on)</sub>	-	3.27	-	ns		
Turn-On Rise Time	t <sub>r</sub>	-	3.15	-	ns	$V_{DD} = 30V, V_{GEN} = 10V,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	12.025	-	ns	$R_{GEN} = 25\Omega, I_D = 0.115A$	
Turn-Off Fall Time	t <sub>f</sub>	-	6.29	-	ns		

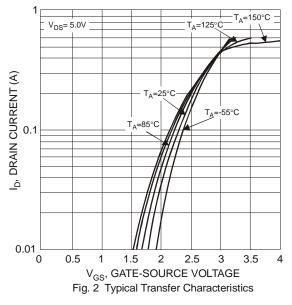
- Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
  Device mounted on 2" x 2" FR-4 PCB with high coverage 2 oz. Copper, single sided.
  Short duration pulse test used to minimize self-heating effect.
  Guaranteed by design. Not subject to production testing.

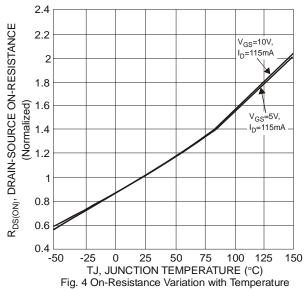


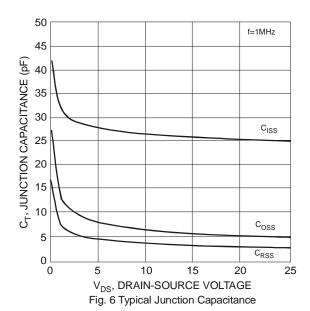




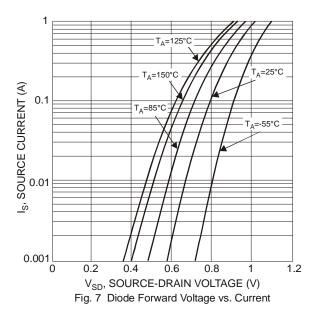




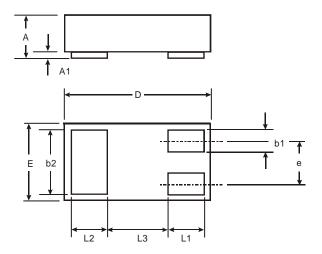






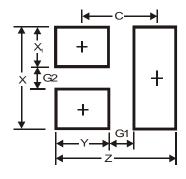


# **Package Outline Dimensions**



DFN1006								
Dim	Min	Max	Тур					
Α	0.47	0.53	0.50					
A1	0	0.05	0.03					
b1	0.10	0.20	0.15					
b2	0.45	0.55	0.50					
D	0.95	1.075	1.00					
Е	0.55	0.675	0.60					
е			0.35					
L1	0.20	0.30	0.25					
L2	0.20	0.30	0.25					
L3			0.40					
All Dimensions in mm								

# Suggested Pad Layout



Dimensions	Value (in mm)			
Z	1.1			
G1	0.3			
G2	0.2			
Х	0.7			
X1	0.25			
Υ	0.4			
С	0.7			



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